

TENTATIVE**SBD MODULE 80A/150V****P2H80QH15**

FEATURES

- * Compatible with Isolated Base SOT227
- * Dual Separated Diodes
- * Extremely Low Forward Voltage Drop
- * Low Power Loss, High Efficiency
- * High Surge Capability

OUTLINE DRAWING

See the Next Page

TYPICAL APPLICATIONS

- * High Frequency Rectification

Maximum Ratings

Approx Net Weight:35g

Parameter	Symbol	Type / Grade		Unit
		P2H80QH15	-	
Repetitive Peak Reverse Voltage *1	V _{RRM}	150	-	V
Non Repetitive Peak Reverse Voltage *1	V _{RSM}	-	-	

Parameter		Conditions	Max Rated Value	Unit
Average Rectified Output Current *1	I _{O(AV)}	50Hz Half Sine Wave condition T _c =T _o Be Determined	80	A
Surge Forward Current *1	I _{FSM}	50 Hz Half Sine Wave, 1Pulse Non-repetitive	800	A
Operating Junction Temperature Range	T _{jw}		-40 to +150	°C
Storage Temperature Range	T _{stg}		-40 to +125	°C
Isolation Voltage	V _{iso}	Base Plate to Terminals, AC1min	2500	V
Mounting torque	Terminals	M4Screw	1.5(1.4)	N.m
	Case mounting	M4Screw with Thermal Compound	1.5(1.4)	

Electrical • Thermal Characteristics

Characteristics	Symbol	Test Conditions	Max.	Unit
Peak Reverse Current *1	I _{RM}	V _{RM} = V _{RRM} , T _j = 25°C	60	μA
Peak Forward Voltage *1	V _{FM}	I _{FM} = 80A, T _j =25°C	1.02	V
Thermal Resistance *1	R _{th(j-c)}	Junction to Case	0.53	°C/W
	R _{th(c-f)}	Base Plate to Heat Sink with Thermal Compound	0.3	

*1: Value Per 1Arm

P2H80QH15 OUTLINE DRAWING (Dimensions in mm)

